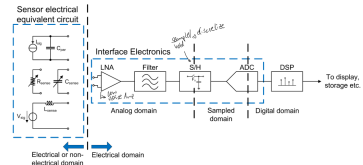


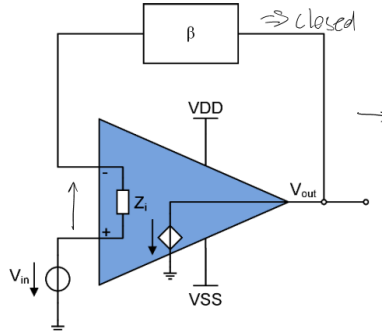
Sensor Principles

A generic sensor interface



OPAMP Basics

Opamps in feedback



Gain: $T(\omega) = \beta \cdot A_0(\omega)$
 Phase Margin:
 $PM = 180^\circ + \angle(T(\omega_1)) |_{|T(\omega_1)|=1}$ Gain margin: $GM = 20 \cdot \log_{10} \left(\frac{1}{|T(\omega_2)|} \right) |_{\angle(T(\omega_2)) = -180^\circ}$ **Generic**

Transfer function
 $V_x = \beta \cdot V_{out} = \beta \cdot A(\omega) \cdot (V_{in} - V_x) = \beta \cdot A(\omega) \cdot (V_{in} - \beta \cdot V_{out})$
 $\frac{V_{out}}{V_{in}} = \frac{A(\omega)}{1 + \beta \cdot A(\omega)} \approx \frac{A(\omega)}{\beta} \gg 1$ **Negative**

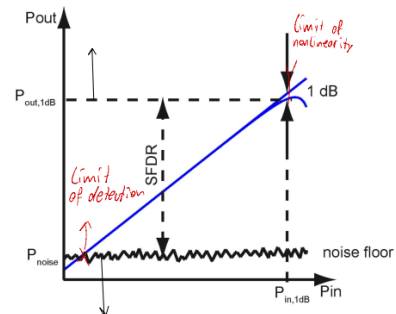
Feedback and linear operation

$A(\omega) \gg 1 \Rightarrow$ virtual short at the input
 $\Delta V \approx 0$
 $Z_i \rightarrow \infty \Rightarrow i_{oa} \approx 0$
 Voltage Drive \rightarrow negative feedback
 Current drive \rightarrow positive feedback

Errors and Noise

Limit of detection (LOD): minimum measurable input amplitude ($SNR \approx 0$)

Dynamic range (DR): ratio of max and min amplitude within inaccuracy levels.



Error types:

Deterministic: source loading, offset, gain error
 Random: thermal noise, 1/f noise

Quantification:

Absolute: $\Delta x = |\hat{x} - x_0|$

Relative: $\left| \frac{\Delta x}{x_0} \right| = \left| \frac{\hat{x} - x_0}{\hat{x}} \right|$

Max inaccuracy:

$\Delta x_{max} | x \in [\hat{x} - \Delta x_{max}, \hat{x} + \Delta x_{max}]$

Error Propagation

$y = f(x_1, x_2, \dots, x_N)$

Deterministic fluctuations of $x_i \rightarrow$ total error:

$\Delta y \approx \sum_{i=1}^N \frac{\partial f}{\partial x_i} \cdot \Delta x_i$

Partial derivative $\frac{\partial f}{\partial x_i}$ is called **sensitivity**

Additive errors are best specified absolute and multiplicative errors are best specified relative

Interference:

Unwanted coupling of external signal

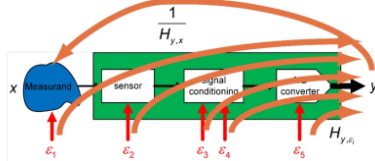
Noise: random fluctuations from setup \rightarrow can be modeled as error sources

Combining Error sources

Output referred noise

Effect of an error-source on the output

Input referred noise Equivalent effect of the error-source on the input



Find TF from ES to output

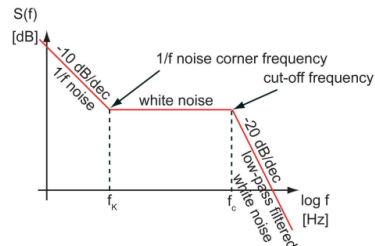
$y: H_{y,ES} \Rightarrow y_{out}, e_2 = H_{y,e_2} \cdot e_2$

Refer result back to input wit

$H_{y,x}: x_{e2} = \frac{y_{out}, e_2}{H_{y,x}} = H_{y,e_2} \cdot \frac{e_2}{H_{y,x}}$

Lin. System noise:

$PSD = S_y(f) = |H(f)|^2 \cdot S_x(f)$



Noise Types

Thermal noise: excitation of charge carriers (white)

Shot noise: carriers randomly crossing the barrier, dependent on DC bias and white

Flicker Noise: due to traps in semiconduct. 1/f spectral density. MOS trans at low freq.

Thermalnoise Theorem: Every closed system at temp. T has average. Energy of $kT/2 \rightarrow$

$S_u(f) = 2kTR$ (double-sided) math

$S_u(f) = 4kTR$ (single-sided) physics

Langevin Approach kt/C noise

PSD noise voltage of V_n

$= S_{v_n}(f) = 4kT \cdot \Re\{Z(j2\pi f)\}$

$\rightarrow \overline{V_n^2} = kT \left[\frac{1}{C_\infty} - \frac{1}{C_0} \right] = \frac{kT}{C}$

MOS IRN

$S_{\Delta V_{nG-tot}} = 4kT \cdot R_{nG-tot}, R_{nG-tot} =$

$\frac{\rho}{W \cdot L \cdot f} + \frac{\gamma_n D}{G_m}$ with GateExcess Noise factor

$\gamma_n D = (n - 1.3) \cdot [0.5 W I; 2/3 S I]$

Bipolar Trans IRN:

$S_{\Delta V_{nR}}^2 = 4kT \cdot R_B$

Noise Analysis

small-signal-equivalent is valid.

Total ORN:

$S_{n,out}(f) = \sum_{k=1}^N |H_k(f)|^2 \cdot S_{n_k}(f)$

N uncorrelated NS.

$H_k(f)$ TF from NS ton output. IRN:

$S_{V_{neq,IRN}}(f) = \frac{S_{V_{out}}(f)}{|A(f)|^2}$ with $A(f)$ is TF

Sensor types

Information domain \rightarrow Electrical domain

Transduction: Converting a signal from the energy domain into another.

Sensors and actuators are transducers

Sources of error

Noise, sensitivity to unintended quantities,

Noise, EMI

$$\begin{pmatrix} E_{meas} \\ E_{mech} \\ E_{chem} \\ E_{opt} \\ E_{elec} \end{pmatrix} = \begin{pmatrix} \sigma_{meas,meas} & \sigma_{meas,mech} & \sigma_{meas,therm} & \sigma_{meas,opt} & \sigma_{meas,elec} \\ \sigma_{mech,meas} & \sigma_{mech,mech} & \sigma_{mech,therm} & \sigma_{mech,opt} & \sigma_{mech,elec} \\ \sigma_{chem,meas} & \sigma_{chem,mech} & \sigma_{chem,therm} & \sigma_{chem,opt} & \sigma_{chem,elec} \\ \sigma_{opt,meas} & \sigma_{opt,mech} & \sigma_{opt,therm} & \sigma_{opt,opt} & \sigma_{opt,elec} \\ \sigma_{elec,meas} & \sigma_{elec,mech} & \sigma_{elec,therm} & \sigma_{elec,opt} & \sigma_{elec,elec} \end{pmatrix} \begin{pmatrix} E_{meas} \\ E_{mech} \\ E_{chem} \\ E_{opt} \\ E_{elec} \end{pmatrix} + \begin{pmatrix} E_{meas,env} \\ E_{mech,env} \\ E_{chem,env} \\ E_{opt,env} \\ E_{elec,env} \end{pmatrix}$$

Resolution: $B_{\min} \hat{=} \frac{V_{\text{noise}}}{V_{\text{hall}}/B} = \frac{\sqrt{4kT \cdot R \cdot \Delta f}}{S_I \cdot I}$

With $S_I = \frac{\mu \cdot \rho}{h \cdot e \cdot n} \cdot G$

At $B = 0$ Hall plate can be modeled as wheatstone bridge, non-uniform stress causes intrinsic offset(5 to 30mT)

Cancel intrinsic offset by coupling ° turned

sensors, current and sense ports are swapped

Idea: Hall voltage is in phase and gradient

caused offsets are than 180° out of phase

Spinning current method:

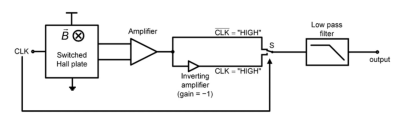
Sense and current ports are switched every clock cycle

Idea: A DC component equal to the offset and a frequency component proportional to the hall voltage is produced (**Fourier Expansion of a square wave**)

By modulating the information to the clock

frequency noise and offset are greatly

mitigated.



Multiplying by 1 and -1 to demodulate back to

low frequency.

Low pass stage to remove signal around the

2nd harmonic

This allow to see the base noise floor of the sensor not 1/f noise.

In the conventional implementation 2 bias

currents are used in the low power

configuration the bias form the plate is reused for the amplifier.

Temperature Sensors

Seebeck effect: Convert temp. gradient to

electromotive force

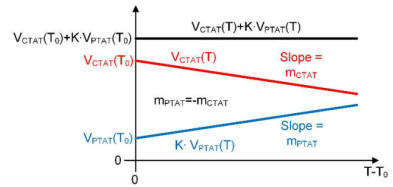
$$F(T) \doteq \int_{T_{stand.}}^T (S_+(T') - S_-(T')) dT'$$

$$\rightarrow E_{emf} = F(T_{sense} - F(T_{ref}))$$

Temperature stable references:

$$V_{\text{REF}}(T) = V_{\text{CTAT}}(T) + K \cdot V_{\text{PTAT}}(T)$$

Bandgap reference:



PTAT: Proportional to absolute temperature

CTAT: Complementary to absolute temperature

Scale one slope and add the function for a

temp. constant reference

This can be built with a diode or a BJT with a

shorted base and collector

Butt current is also temperature dependent so

use diff pair.

$$V_{\text{PTAT}} = \Delta V_{\text{EB}} = V_{\text{EB1}} - V_{\text{EB2}} \approx$$

$$\frac{kT}{q} \cdot \ln \left[\frac{I_q \cdot I'_S \cdot A_{E2}}{I'_S \cdot A_{E1} \cdot I_q} \right] = \frac{kT}{q} \cdot \ln \left[\frac{A_{E2}}{A_{E1}} \right]$$

Scale currents or diodes to make equal bias

$$V_{\text{EB}} = \underbrace{E_g/q}_{V_G} - \underbrace{\frac{kT}{q}}_{U_T} \cdot \ln \left(\frac{I'_s}{I_D} \right) =$$

$$V_G - U_T \cdot \ln \left(\frac{K_1 \cdot T^\gamma}{I_D} \right)$$

$$V_G \approx V_{G0K} - a \cdot T$$

With $I'_S > I_D$ but also temperature

dependent → curved CTAT.

Combine CTAT and PTAT: Series:

$$V_{\text{REF}} = I_{\text{PTAT}} \cdot R_2 + V_{\text{CTAT}} =$$

$$\frac{R_2}{R_1} \cdot V_{\text{PTAT}} + V_{\text{CTAT}}$$

Parallel:

$$V_{\text{REF}} = (I_{\text{PTAT}} + I_{\text{CTAT}}) \cdot R_3 =$$

$$\frac{R_3}{R_1} \cdot V_{\text{PTAT}} + \frac{R_3}{R_2} \cdot V_{\text{CTAT}}$$